

**TRANSISTOR(PNP)****FEATURES**

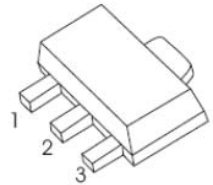
- High Collector Current
- Complementary to SS8050

MARKING: Y2

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}C/W$
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$

SOT-89

1. BASE
2. COLLECTOR
3. EMITTER

**ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)**

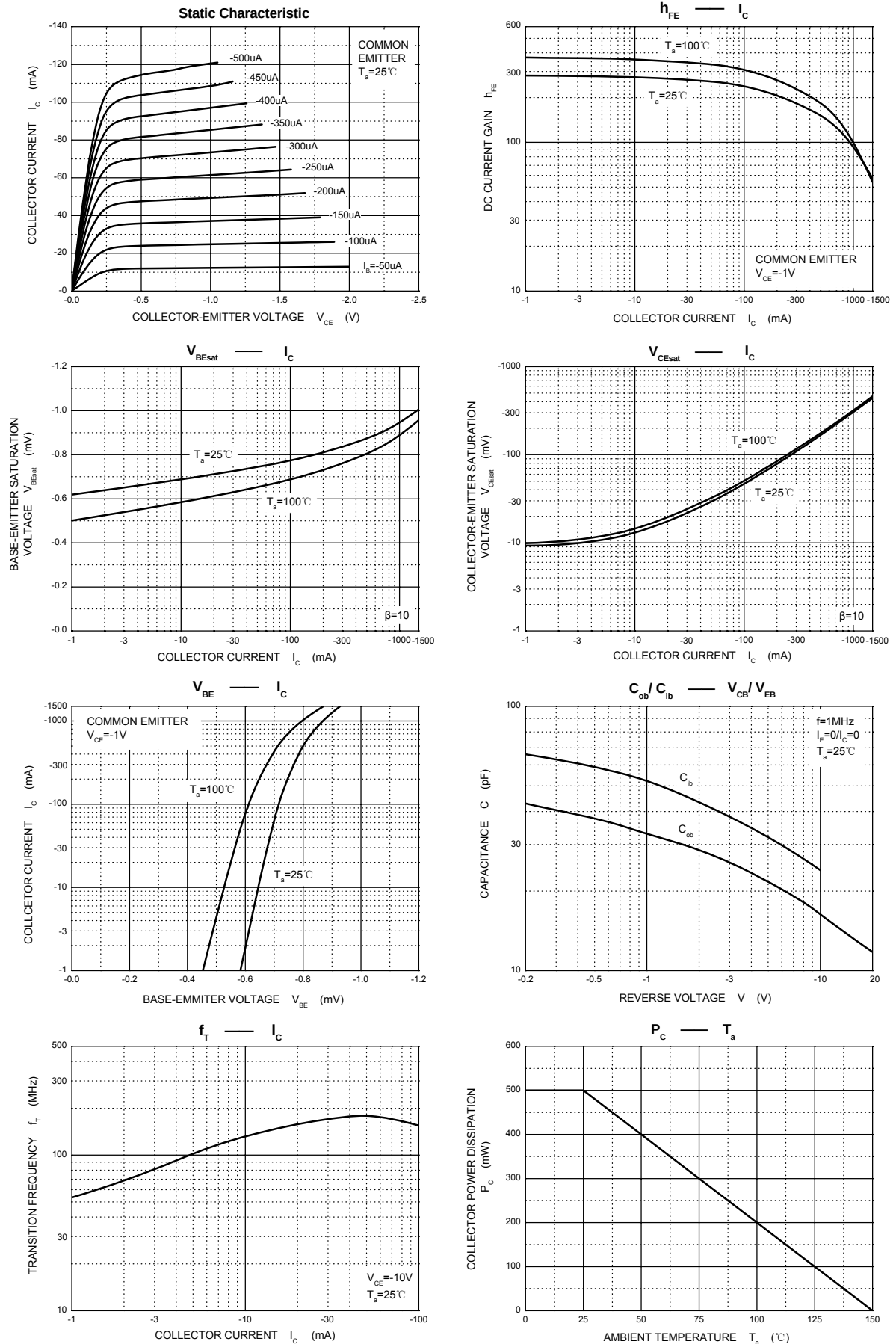
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	120		400	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$			-1	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=30MHz$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF

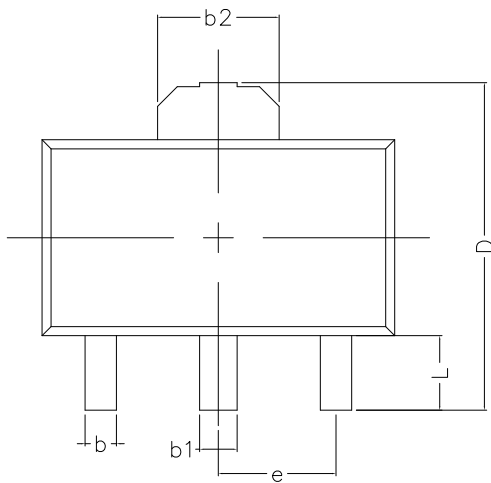
CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400

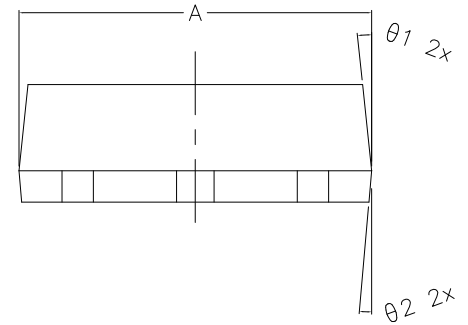
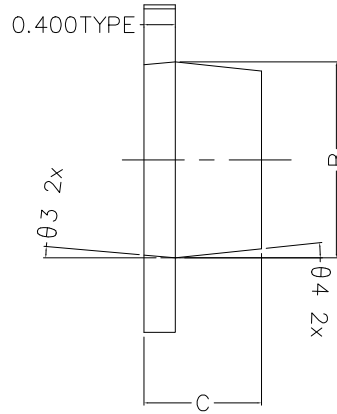


Typical Characteristics





TOP VIEW



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.450	4.550	4.650
B	2.450	2.550	2.650
C	1.400	1.500	1.600
D	4.100	4.200	4.300
L	0.850	0.950	1.050
b	0.350	0.400	0.450
b1	0.430	0.480	0.530
b2	1.500	1.550	1.600
e	1.500TYPE		
θ_1	6° TYPE		
θ_2	5° TYPE		
θ_3	5° TYPE		
θ_4	6° TYPE		